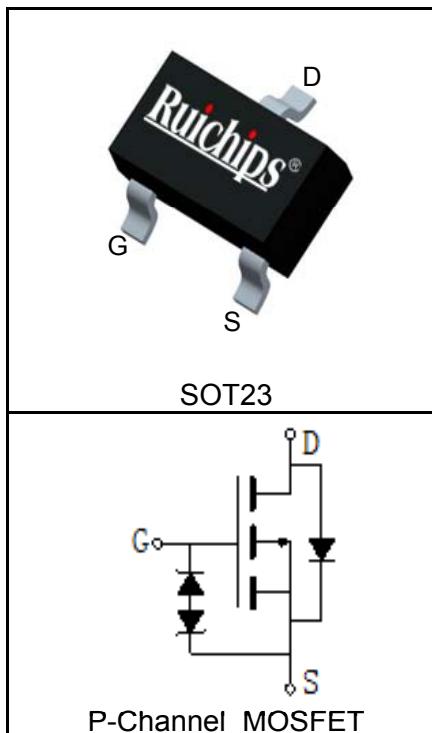


### Features

- -12V/-4A,
- $R_{DS\ (ON)} = 28m\Omega$ (Typ.)@ $V_{GS}=-4.5V$
- $R_{DS\ (ON)} = 35m\Omega$ (Typ.)@ $V_{GS}=-2.5V$
- Low On-Resistance
- ESD protected
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

### Pin Description



### Applications

- Load Switch
- Power Management
- Battery Protection

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_A=25^\circ C$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	-12	V
$V_{GSS}$	Gate-Source Voltage	$\pm 10$	
$T_J$	Maximum Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$I_S$	Diode Continuous Forward Current	$T_A=25^\circ C$	-1
			A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}^{(1)}$	300 $\mu$ s Pulse Drain Current Tested	$T_A=25^\circ C$	-16
$I_D^{(2)}$	Continuous Drain Current( $V_{GS}=-4.5V$ )	$T_A=25^\circ C$	-4
		$T_A=70^\circ C$	-3.2
$P_D$	Maximum Power Dissipation	$T_A=25^\circ C$	1.3
		$T_A=70^\circ C$	0.8
$R_{\theta JC}$	Thermal Resistance-Junction to Case	-	$^\circ C/W$
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	125	$^\circ C/W$
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	TBD	mJ

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  Unless Otherwise Noted)

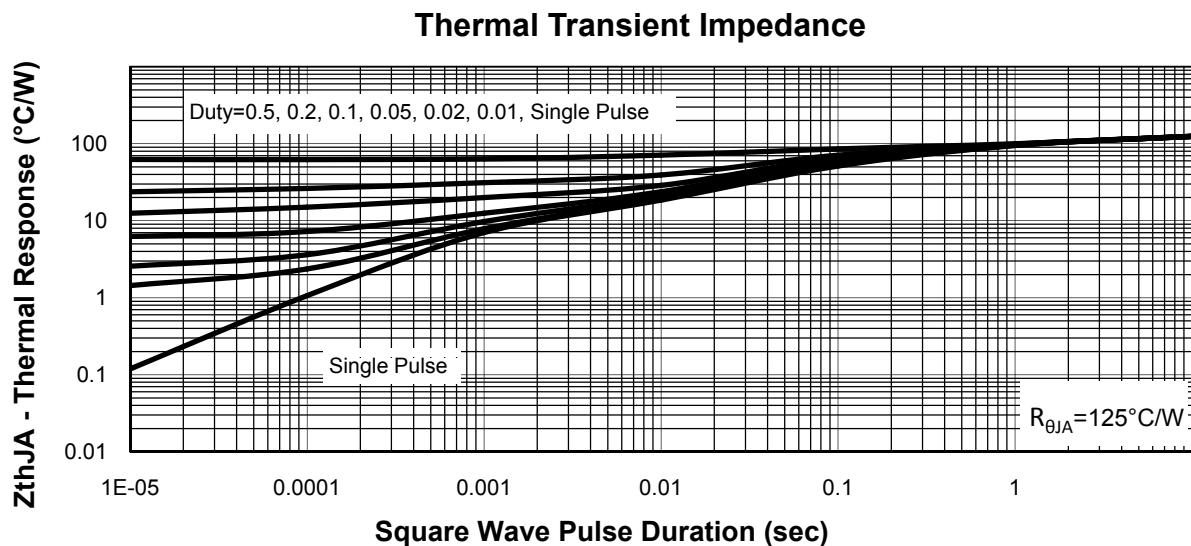
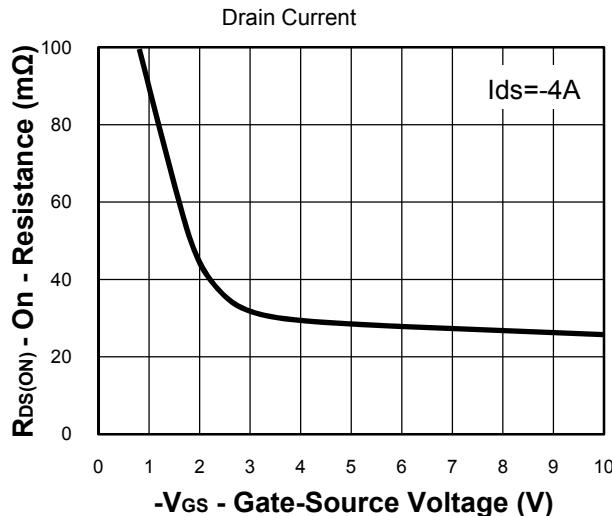
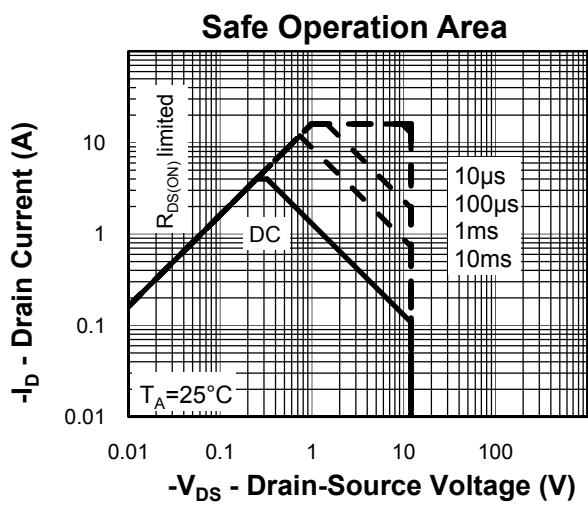
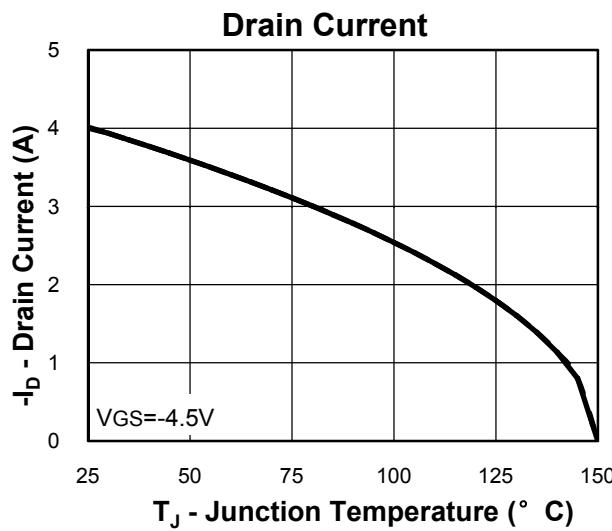
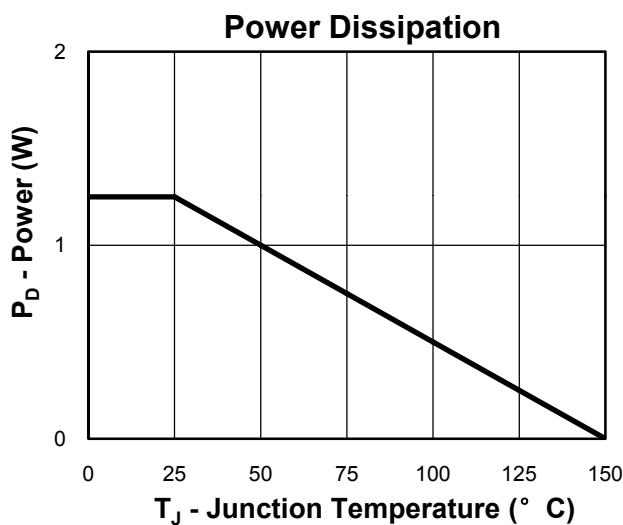
Symbol	Parameter	Test Condition	RU3415B			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{DS}}=-250\mu\text{A}$	-12	-16		V
$\text{I}_{\text{DSS}}$	Zero Gate Voltage Drain Current	$\text{V}_{\text{DS}}=-12\text{V}, \text{V}_{\text{GS}}=0\text{V}$			-1	$\mu\text{A}$
		$\text{T}_J=125^\circ\text{C}$			-30	
$\text{V}_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{DS}}=-250\mu\text{A}$	-0.4		-1	V
$\text{I}_{\text{GSS}}$	Gate Leakage Current	$\text{V}_{\text{GS}}=\pm 10\text{V}, \text{V}_{\text{DS}}=0\text{V}$			$\pm 10$	$\mu\text{A}$
$\text{R}_{\text{DS(ON)}}^{(5)}$	Drain-Source On-state Resistance	$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{DS}}=-4\text{A}$		28	40	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-2.5\text{V}, \text{I}_{\text{DS}}=-3\text{A}$		35	50	$\text{m}\Omega$
<b>Diode Characteristics</b>						
$\text{V}_{\text{SD}}^{(5)}$	Diode Forward Voltage	$\text{I}_{\text{SD}}=-1\text{A}, \text{V}_{\text{GS}}=0\text{V}$			-1.2	V
$\text{t}_{\text{rr}}$	Reverse Recovery Time	$\text{I}_{\text{SD}}=-4\text{A}, \frac{d\text{I}_{\text{SD}}}{dt}=100\text{A}/\mu\text{s}$		19		ns
$\text{Q}_{\text{rr}}$	Reverse Recovery Charge			26		nC
<b>Dynamic Characteristics</b> <sup>(6)</sup>						
$\text{R}_G$	Gate Resistance	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=0\text{V}, \text{F}=1\text{MHz}$		1.6		$\Omega$
$\text{C}_{\text{iss}}$	Input Capacitance	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=-8\text{V}, \text{Frequency}=1.0\text{MHz}$		640		$\text{pF}$
$\text{C}_{\text{oss}}$	Output Capacitance			115		
$\text{C}_{\text{rss}}$	Reverse Transfer Capacitance			75		
$\text{t}_{\text{d(ON)}}$	Turn-on Delay Time	$\text{V}_{\text{DD}}=-8\text{V}, \text{I}_{\text{DS}}=-4\text{A}, \text{V}_{\text{GEN}}=-4.5\text{V}, \text{R}_G=6\Omega$		9		ns
$\text{t}_{\text{r}}$	Turn-on Rise Time			16		
$\text{t}_{\text{d(OFF)}}$	Turn-off Delay Time			29		
$\text{t}_{\text{f}}$	Turn-off Fall Time			19		
<b>Gate Charge Characteristics</b> <sup>(6)</sup>						
$\text{Q}_g$	Total Gate Charge	$\text{V}_{\text{DS}}=-10\text{V}, \text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{DS}}=-4\text{A}$		9.5		nC
$\text{Q}_{\text{gs}}$	Gate-Source Charge			1.8		
$\text{Q}_{\text{gd}}$	Gate-Drain Charge			2.9		

- Notes:
- ①Pulse width limited by safe operating area.
  - ②Calculated continuous current based on maximum allowable junction temperature.
  - ③When mounted on 1 inch square copper board,  $t \leq 10\text{sec}$ . The value in any given application depends on the user's specific board design.
  - ④Limited by  $T_{J\max}$ . Starting  $T_J = 25^\circ\text{C}$ .
  - ⑤Pulse test; Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
  - ⑥Guaranteed by design, not subject to production testing.

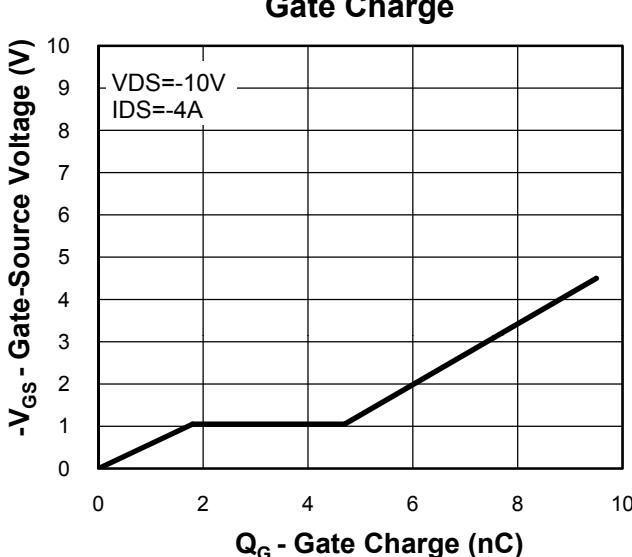
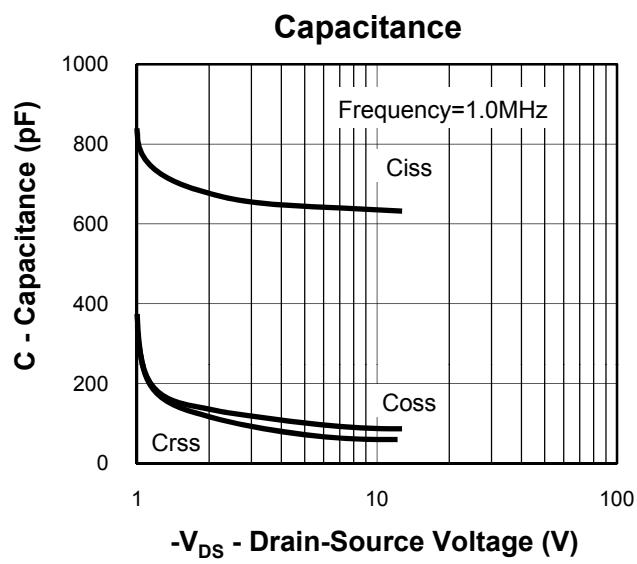
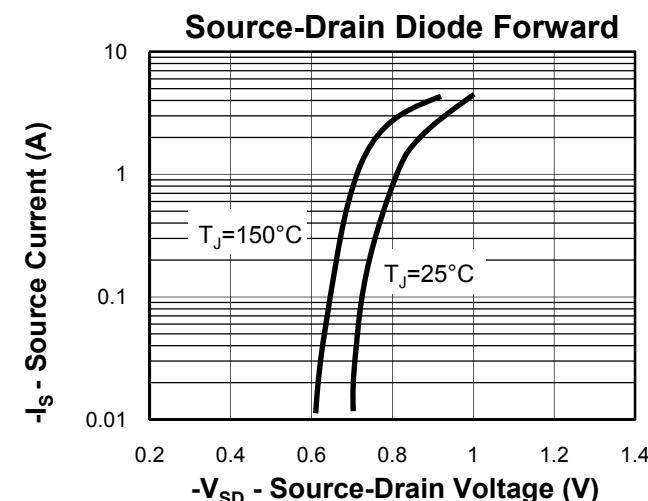
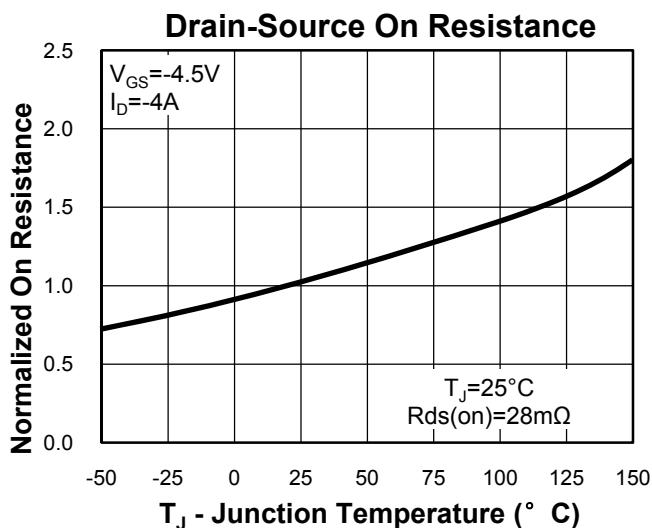
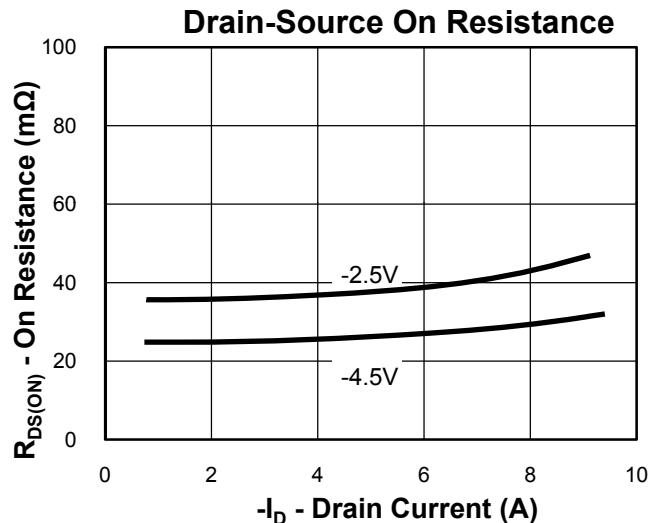
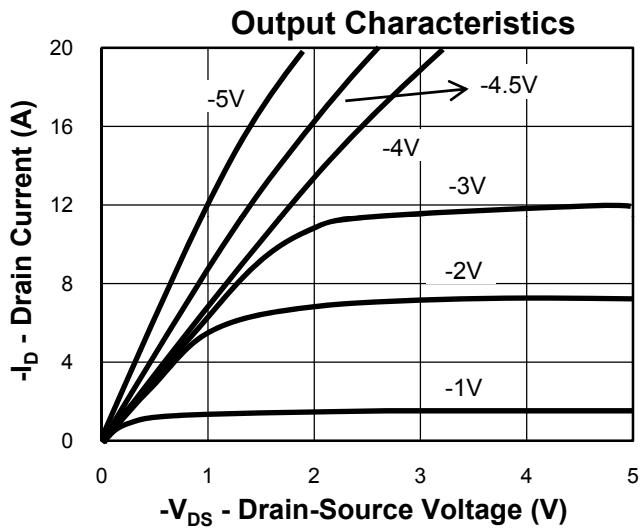
## Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape
RU3415B	RU3415	SOT23	Tape&Reel	3000	7"	8mm

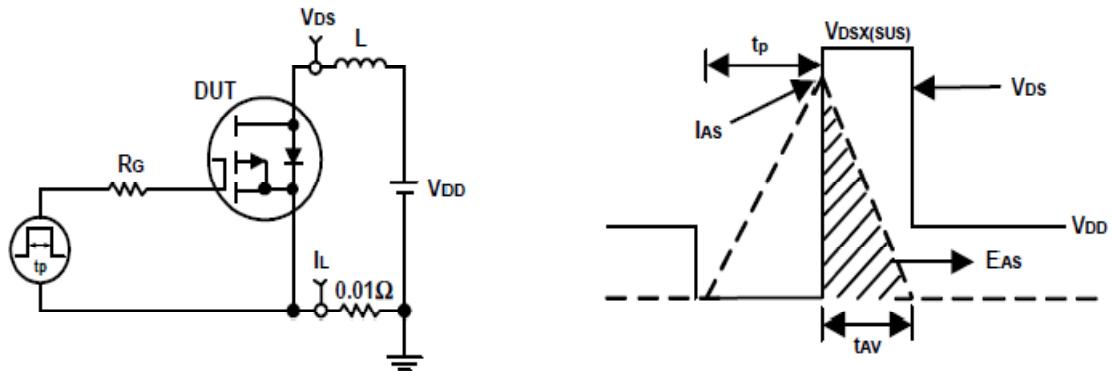
### Typical Characteristics



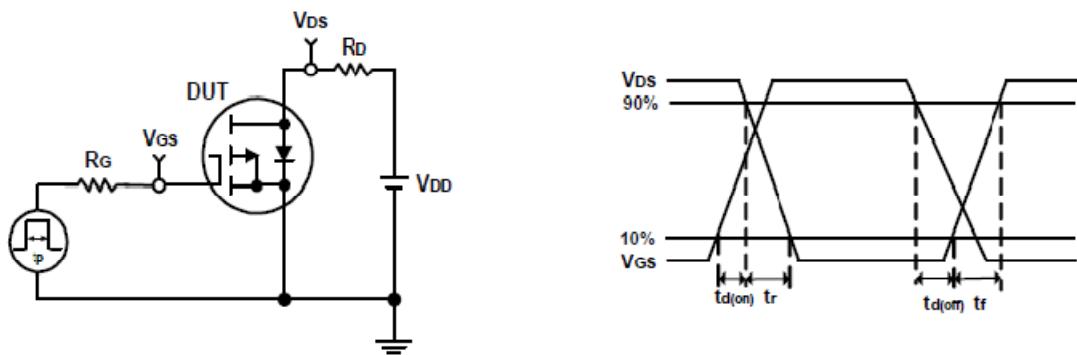
### Typical Characteristics



### Avalanche Test Circuit and Waveforms

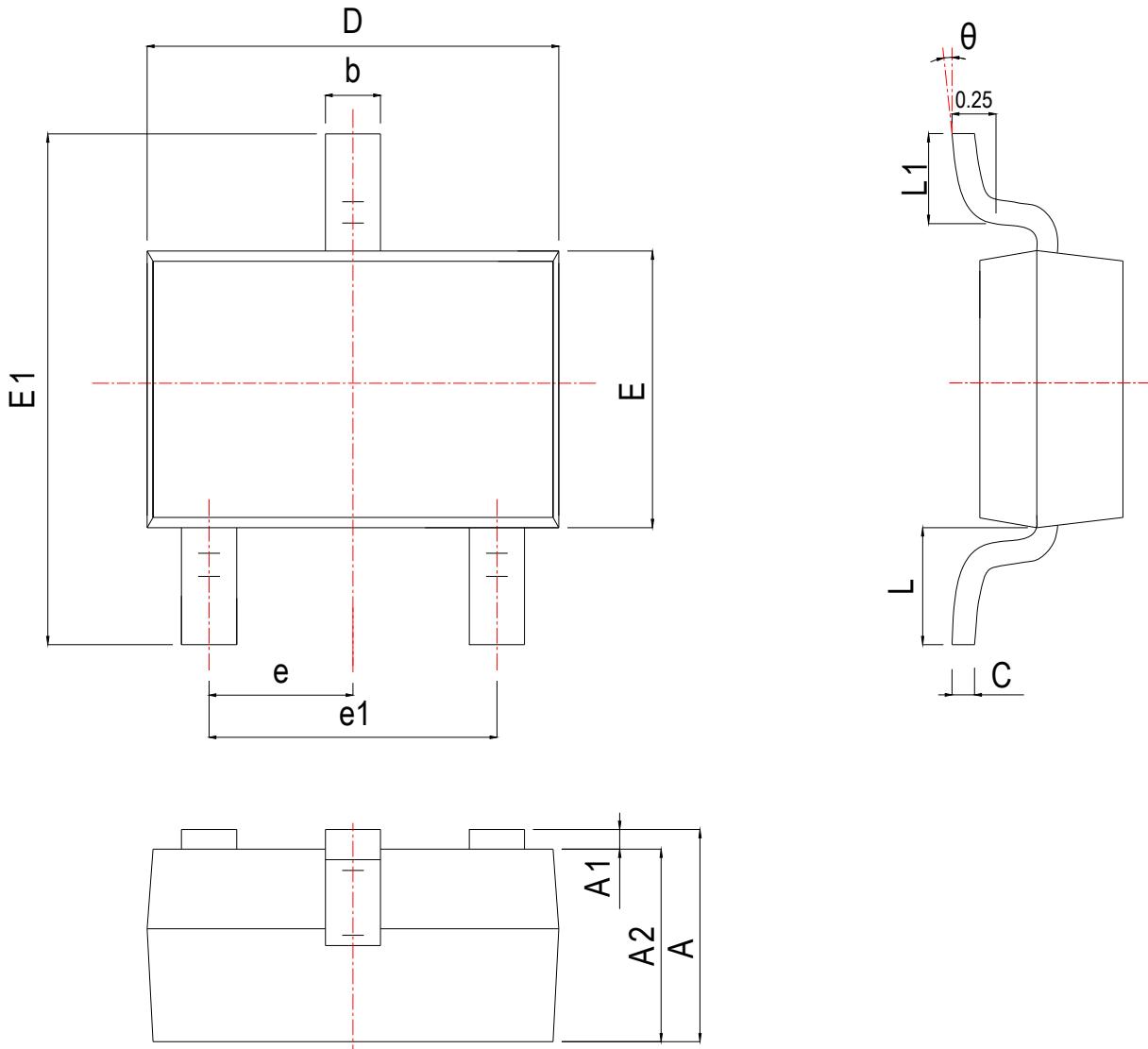


### Switching Time Test Circuit and Waveforms



## Package Information

SOT23



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.900	1.025	1.150	0.035	0.040	0.045
A1	0.050	0.075	0.100	0.002	0.003	0.004
A2	0.900	0.975	1.020	0.035	0.038	0.040
b	0.300	0.400	0.500	0.012	0.016	0.020
c	0.080	0.115	0.150	0.003	0.005	0.006
D	2.800	2.900	3.000	0.110	0.114	0.118
E	1.200	1.300	1.400	0.047	0.051	0.055
E1	2.250	2.400	2.550	0.089	0.094	0.100
e	0.950 TYP			0.037 TYP		
e1	1.800	1.900	2.000	0.071	0.075	0.079
L	0.540 REF			0.021 REF		
L1	0.400	0.500	0.600	0.016	0.018	0.020
theta	0°	*	8°	0°	*	8°

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